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SOT23 NPN SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

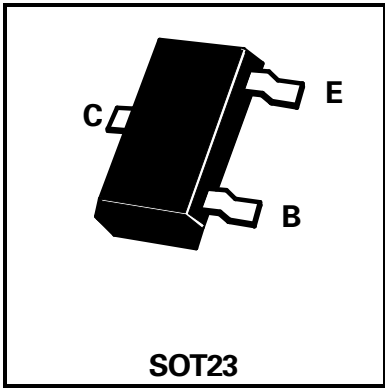
FMMT455

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FEATURES

- * 140 Volt V_{CEO}
- * 1 Amp continuous current
- * $P_{tot} = 500$ mW

PARTMARKING DETAIL – 455



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	140	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Base Current	I_B	200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	160		V	$I_C = 100\mu\text{A}$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	140		V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		0.1	μA	$V_{CB} = 140\text{V}$
Emitter Cut-Off Current	I_{EBO}		0.1	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.7	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	100 10 Typ	300		$I_C = 150\text{mA}, V_{CE} = 10\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 10\text{V}^*$
Transition Frequency	f_T	100		MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		15	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
 Spice parameter data is available upon request for this device

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TYPICAL CHARACTERISTICS

